

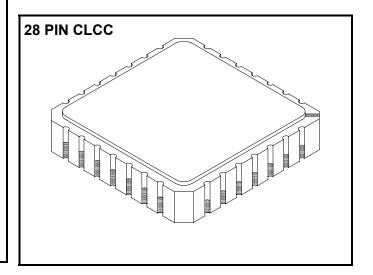
Designer's Data Sheet

FEATURES:

- Extremely Low Forward Voltage Drop
- Low Reverse Leakage
- Hermetically Sealed Surface Mount Package
- Guard Ring for Overvoltage Protection
- Ceramic Seals for Improved Hermeticity
- Custom Lead Forming Available
- Eutectic Die Attach
- 175°C Operating Junction Temperature
- Also Available in the following configurations:
 - Common Cathode Centertap: SSR1010-28CT
 - Common Anode Centertap: SSR1010-28CA
 - Doubler: SSR0510-28D
- TX, TXV, and Space Level Screening Available

SSR1008-28
SSR1009-28
SSR1010-28

10 AMPS 80-100 VOLTS SCHOTTKY RECTIFIER



MAXIMUM RATINGS			Value	Units
Peak Repetitive Reverse Voltage and DC Blocking Voltage	SSR1008-28 SSR1009-28 SSR1010-28	V _{RRM} V _{RWM} V _R	80 90 100	Volts
Average Rectified Forward Current (Resistive Load, 60 Hz, Sine Wave, $T_A=25^{\circ}C$)		I _O	10	Amps
Peak Surge Current (8.3 ms Pulse, Half Sine Wave Superimposed on I_0 , allow junction to reach equilibrium between pulses, $T_A=25^{\circ}C$)		I _{FSM}	200	Amps
Operating and Storage Temperature		T _{OP} & Tstg	-65 to +175	°C
Maximum Thermal Resistance Junction to Case		R _{θJC}	6.0	°C/W

NOTE: All specifications are subject to change without notification. SCD's for these devices should be reviewed by SSDI prior to release.	DATA SHEET #: RS0195B	DOC
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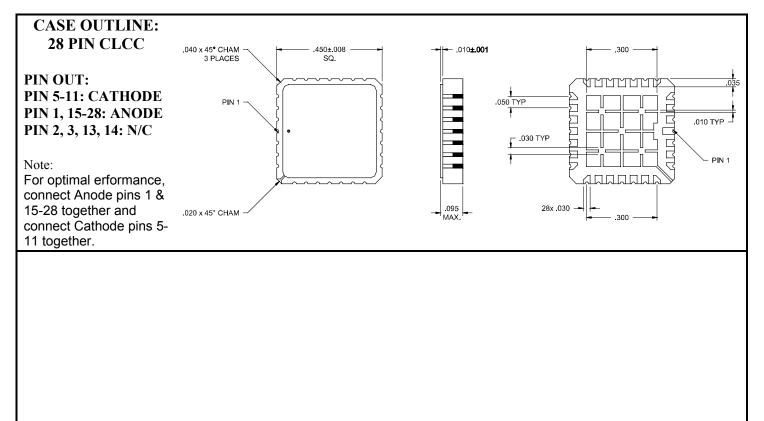


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SSR1008-28 SSR1009-28 SSR1010-28

ELECTRICAL CHARACTERISTICS		Symbol	Max	Unit
Instantaneous Forward Voltage Drop (T _A = 25 °C, Pulse)	$I_F = 1 \text{ Amps}$ $I_F = 5 \text{ Amps}$ $I_F = 10 \text{ Amps}$	$egin{array}{c} V_{F1} \ V_{F2} \ V_{F3} \end{array}$	0.56 0.72 0.82	Volts
Instantaneous Forward Voltage Drop $(I_F = 10 \text{ Amps}, T_A = -55 \text{ C}, \text{Pulse})$		V_{F4}	0.87	Volts
Reverse Leakage Current (Rated V_R , $T_A = 25$ °C, Pulse)		I _{R1}	100	μA
Reverse Leakage Current (Rated V_R , $T_A = 100$ °C, Pulse)		I _{R2}	5	mA
Junction Capacitance ($V_R = 10 V_{DC}, T_A = 25^{\circ}C, f = 1 MHz$)		CJ	400	pF



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